PROCESS CP214

Small Signal Transistor

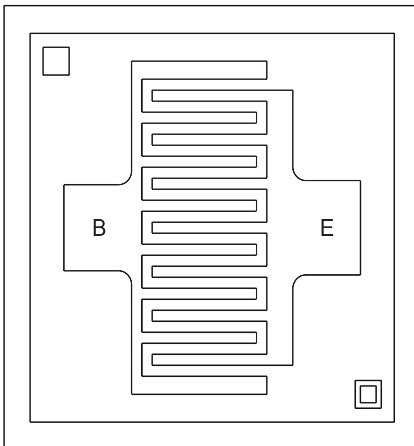
NPN - Silicon RF Transistor Chip

Central™
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	16 x 16 MILS
Die Thickness	7.5 MILS
Base Bonding Pad Area	2.9 x 3.4 MILS
Emitter Bonding Pad Area	2.9 x 3.4 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 16,000Å

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER
44,460

PRINCIPAL DEVICE TYPES
2N5109

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Hauppauge, NY 11788 USA
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www.centralsemi.com

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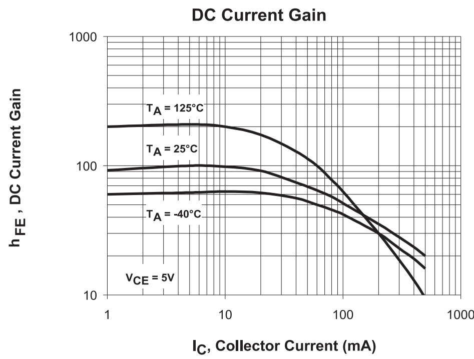
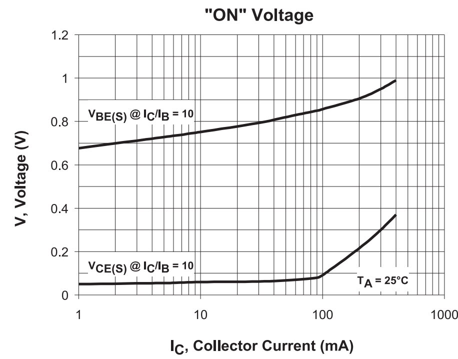
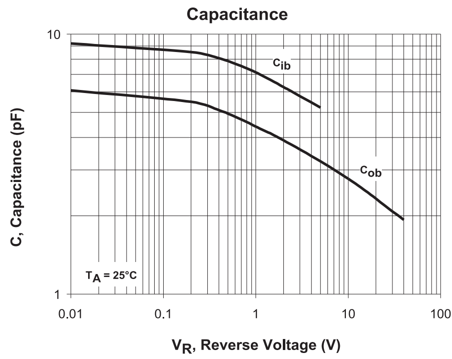
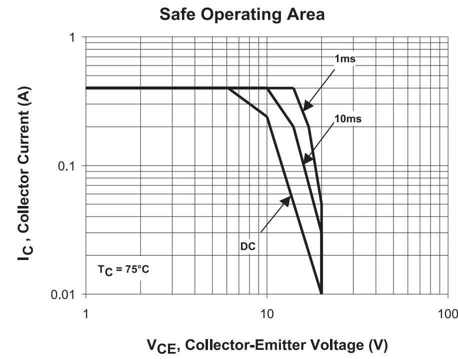
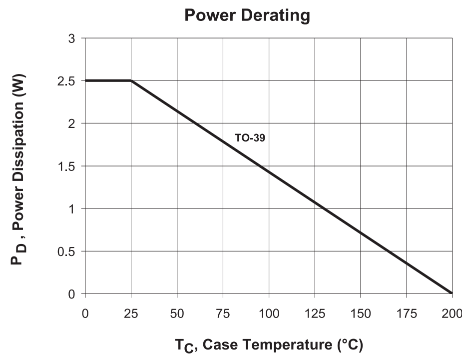
Typical Electrical Characteristics

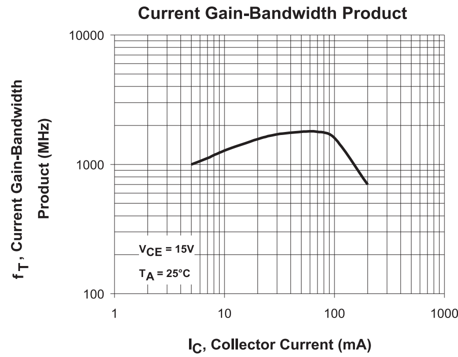












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